

ABSTRACT

There is provided an underlayer coating forming composition for lithography that is used in lithography process of manufacture of semiconductor device; and an underlayer coating having a high dry etching rate compared with photoresist. Concretely, it is a composition for forming an underlayer without use of crosslinking reaction by an strong acid catalyst, and an underlayer coating forming composition containing a component having an epoxy group (a polymer, a compound) and a component having a phenolic hydroxyl group, a carboxyl group, a protected carboxyl group or an acid anhydride structure (a polymer, a compound).